## SPECIFICATION AMENDMENTS:

Please replace the present ABSTRACT OF THE DISCLOSURE, Page 68, with the Replacement Sheet 68 attached hereto.

On Page 18 of the Specification, please amend Equation 4 as follows:

$$CH_2 = C$$
 $CH_3$ 
 $CH_3$ 
 $CH_3$ 
 $CH_3$ 
 $CCCH_3$ 
 $CCCCH_3$ 
 $CCCCCCC$ 
 $CCCCCCC$ 
 $CCCCCC$ 
 $CCCCCC$ 
 $CCCCC$ 
 $CCCC$ 
 $CCC$ 
 $CC$ 
 $CCC$ 
 $CCC$ 
 $CC$ 
 $C$ 

Please amend the paragraph appearing at page 27, which includes lines 9 and 10 thereof, to read as follows:

Then, after the removal of the covering resin 7 by dissolution, the mold pattern 3 is irradiated, as shown in Fig. 1E, by an ionizing radiation of a wavelength of 300 nm or less across the liquid flow path <u>in</u> structure member 4 constituted of a hardened portion by the pattern exposure to the negative-working photosensitive material layer. Such irradiation intends to decompose the crosslinked positive-working resist constituting the mold pattern 3 to a lower molecular weight, thereby enabling easy removal thereof.

Please amend Page 45 as shown on the attached Replacement Sheet.

A-187 (Nihon Unicar Inc.) 4 parts by weight SP-170 (Asahi Denka Industries Co.)

2 parts by weight

Diethylene glycol monoethyl ether

5 100 parts by weight

Then the liquid flow path structure material 207 and the ink repellent layer were patterned by a pattern exposure by MPA-600 (manufactured by Canon Inc.) with a light of a wavelength of 290 to 400 nm and with an exposure amount of 400 mJ/cm², then a post-exposure bake for 120 seconds at 120°C on a hot plate and a development with methyl isobutyl ketone to form an ink discharge port 209. In the present embodiment, there was formed a discharge port pattern of a diameter of 10 µm.

Then, on the rear surface of the processed substrate, an etching mask [[7]] having an aperture of a width of 1 mm and a length of 10 mm was prepared with a polyetheramide composition (HIMAL, manufactured by Hitachi Chemical Co.). Then the substrate was subjected to an anisotropic etching by immersion in a 22 wt.% TMAH aqueous solution maintained at 80°C, thereby forming an ink supply aperture 210. In this operation, in order to protect the [[ink]] water repellent layer 5 (which also repels ink) from the etching solution, the anisotropic etching was conducted after coating a protective film (OBC manufactured by Tokyo Oka Industries Co.; not